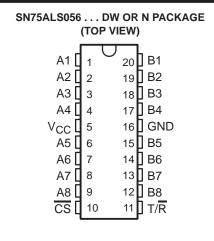
SN75ALS056, SN75ALS057 TRAPEZOIDAL-WAVEFORM INTERFACE BUS TRANSCEIVERS

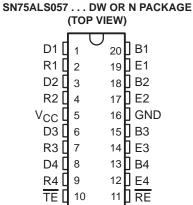
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- Suitable for IEEE Standard 896 Applications†
- SN75ALS056 is an Octal Transceiver
- SN75ALS057 is a Quad Transceiver
- **High-Speed Advanced Low-Power Schottky** (ALS) Circuitry
- **Low Power Dissipation:** 52.5 mW/Channel Max
- **High-Impedance pnp Inputs**
- Logic-Level 1-V Bus Swing Reduces Power Consumption
- **Trapezoidal Bus Output Waveform Reduces Noise Coupling to Adjacent Lines**
- Power-Up/Power-Down Protection (Glitch Free)
- **Open-Collector Driver Outputs Allow Wired-OR Connections**
- Designed to Be a Faster, Lower-Power Functional Equivalent of National DS3896, **DS3897**

description

SN75ALS056 is an eight-channel, monolithic, high-speed, advanced low-power Schottky (ALS) device designed for two-way data communication in a densely backplane. The SN75ALS057 is a four-channel version with independent driver-input (Dn) and receiver-output (Rn) pins and a separate driver disable for each driver (En).





These transceivers feature open-collector driver outputs with series Schottky diodes to reduce capacitive loading to the bus. By using a 2-V pullup termination on the bus, the output signal swing is approximately 1 V, which reduces the power necessary to drive the bus load capacitance. The driver outputs generate trapezoidal waveforms that reduce crosstalk between channels. The drivers are capable of driving an equivalent dc load as low as 18.5 Ω . The receivers have internal low-pass filters to further improve noise immunity.

The SN75ALS056 and SN75ALS057 are characterized for operation from 0°C to 70°C.

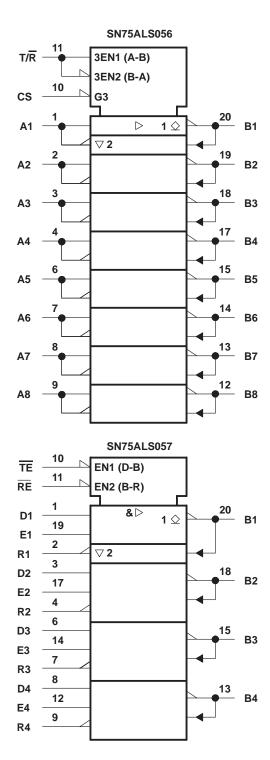


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

† The transceivers are suitable for IEEE Standard 896 applications to the extent of the operating conditions and characteristics specified in this data sheet.



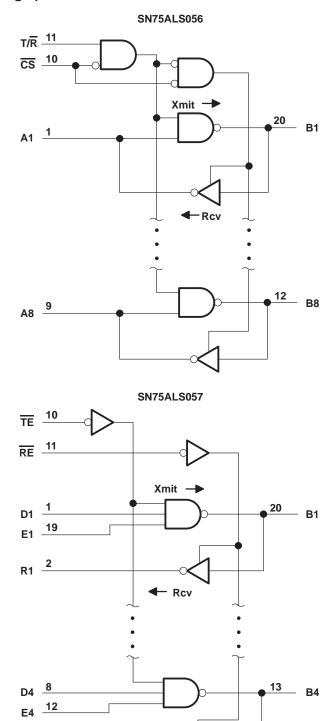
logic symbol†



[†] These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



logic diagram (positive logic)





[†] These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

Function Tables

SN75ALS056 TRANSMIT/RECEIVE

CONT	ROLS	CHANNELS			
CS	T/R	$A \leftrightarrow B$			
L	Н	T(A	B)		
L	L	R(B A)			
Н	Χ)		

SN75ALS057 TRANSMIT/RECEIVE

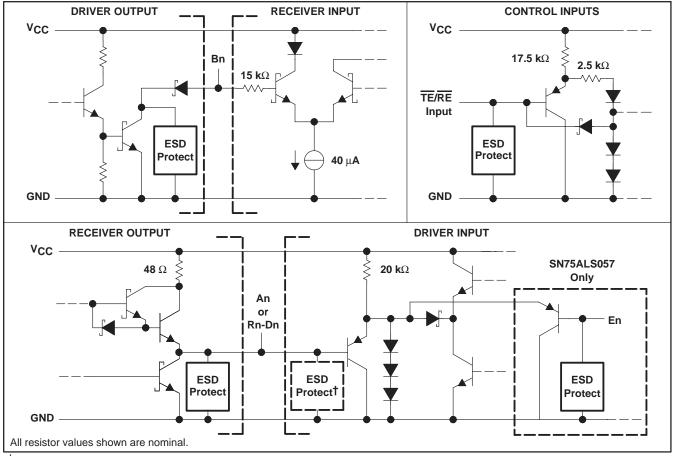
C	ONTROL	.S	CHANNELS				
TE	RE	En	D	В	В	R	
L	L	L)	F	۲	
L	L	Н	1	Γ	F	۲	
L	Н	L)	[)	
L	Н	Н	٦	Γ	[)	
Н	L	Χ)	F	₹	
Н	Н	Χ)	[)	

H = high level, L = low level, R = receive, T = transmit,

D = disable, X = irrelevant

Direction of data transmission is from An to Bn for the SN75ALS056 and from Dn to Bn for the SN75ALS057. Direction of data reception is from Bn to An for the SN75ALS056 and from Bn to Rn for the SN75ALS057. Data transfer is inverting in both directions.

schematics of inputs and outputs



† Additional ESD protection is on the SN75ALS057, which has separate receiver-output and driver-input pins.

absolute maximum ratings over operating free-air temperature (unless otherwise noted)‡

Supply voltage, V _{CC} (see Note 1) 6 V	Supply voltage, V _{CC} (see Note 1
Control input voltage, V _I 5.5 V	Control input voltage, V _I
Oriver input voltage, V _I 5.5 V	Driver input voltage, V _I
Driver output voltage, VO	Driver output voltage, VO
Receiver input voltage, V _I 2.5 V	Receiver input voltage, V _I
Receiver output voltage, V _O 5.5 V	Receiver output voltage, VO
Continuous total power dissipation	Continuous total power dissipation
Storage temperature range, T _{stg} –65°C to 150°C	Storage temperature range, T _{sto}
_ead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DW or N package 260 °C	

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: Voltage values are with respect to network ground terminal.

SN75ALS056, SN75ALS057 TRAPEZOIDAL-WAVEFORM INTERFACE BUS TRANSCEIVERS

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DISSIPATION RATING TABLE

PACKAGE	${ m T_{A}} \le 25^{\circ}{ m C}$ Power rating	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 125°C POWER RATING
DW	1025 mW	8.2 mW/°C	656 mW	_
N	1150 mW	9.2 mW/°C	736 mW	_

recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}	4.75	5	5.25	V
High-level driver and control input voltage, VIH	2			V
Low-level driver and control input voltage, V _{IL}			0.8	V
Bus termination voltage	1.9		2.1	V
Operating free-air temperature, T _A	0		70	°C

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	242445752		TEST SOUDITIONS!	SN	SN75ALS056		
	PARAMETER		TEST CONDITIONS [†]	MIN	TYP [†]	MAX	UNIT
VIK	Input clamp voltage at An,	T/R, or CS	I _I = -18 mA			-1.5	V
VIT	Receiver input threshold v	oltage at Bn		1.405		1.69	V
Vон	High-level output voltage	at An	Bn at 1.2 V, CS at 0.8 V, T/ R at 0.8V, I _{OH} = – 400 μA	2.4			V
	V _{OL} Low-level output voltage	An	Bn at 2 V , CS at 0.8 V, T/R at 0.8 V, I _{OL} = 16 mA			0.5	
VOL		Bn	An at 2 V, \overline{CS} at 0.8 V, T/ \overline{R} at 2 V, V _L = 2 V, R _L =18.5 Ω , See Figure 1	0.75		1.2	V
		An, T/R or CS	$V_I = V_{CC}$			40	
lН	High-level input current	gh-level input current Bn	V _I = 2 V, V _{CC} = 0 or 5.25 V, An at 0.8 V, T/R at 0.8 V			100	μА
Iμ	Low level input current at An, T/R, or CS		V _I = 0.4 V			-400	μΑ
los	Short-circuit output current at An		An at 0, Bn at 1.2 V, CS at 0.8 V, T/R at 0.8 V	-40		-120	mA
Icc	Supply current					75	mA
C _{O(B)}	Driver output capacitance				4.5		pF

[†] Typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

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electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	SN75ALS057			UNIT
	PARAMETER		TEST CONDITIONS	MIN	TYP [†]	MAX	UNII
VIK	Input clamp voltage at Dn, En, T	E, or RE	I _I = -18 mA			-1.5	V
VIT	Receiver input threshold voltage	at Bn		1.41		1.69	V
Vон	High-level output voltage at Rn		Bn at 1.2 V, RE at 0.8 V, I _{OH} = –400 μA	2.4			V
	V _{OL} Low-level output voltage	Rn	Bn at 2 V, RE at 0.8 V, I _{OL} = 16 mA			0.5	
VOL		Bn	Dn at 2 V, En at 2 V, TE at 0.8 V, $V_L = 2 V$, $R_L = 18.5 Ω$, See Figure 1	0.75		1.2	V
		Dn, En <u>,</u> TE, or RE	VI = VCC			40	
Iн	IH High-level input current	Bn	V _I = 2 V, V _{CC} = 0 or 5.25 V, <u>Dn</u> at 0.8 V, En at 0.8 V, <u>TE</u> at 0.8 V			100	μА
Ι _Ι L	Low-level input current at Dn, En	, TE, or RE	V _I = 0.4 V			-400	μΑ
los	Short-circuit output current at Rn		Rn at 0, Bn at 1.2 V, RE at 0.8 V	-40		-120	mA
Icc	Supply current					40	mA
C _{O(B)}	Driver output capacitance				4.5		pF

[†] Typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER		TO	TEST CONDITIONS	SN75ALS056 DRIVER			UNIT
		(INPUT)	(OUTPUT)		MIN	TYP [†]	MAX	
tPLH1	Propagation delay time, low-to-high-level output	cs	Bn	An and T/R at 2 V, V _L = 2 V,			24	20
tPHL1	Propagation delay time, high-to-low-level output	CS	DII	R _L 1 = 18 Ω , C _L = 30 pF, R _L 2 not connected, See Figure 2			20	ns
^t PLH2	Propagation delay time, low-to-high-level output	An	Do	$\overline{\text{CS}}$ at 0.8 V, $\overline{\text{T/R}}$ at 2 V, V _L = 2 V, R _L 1 = 18 Ω ,			19	20
tPHL2	Propagation delay time high-to-low-level output	An	Bn	RL2 not connected, CL = 30 pF, See Figure 2,			18	ns
tPLH3	Propagation delay time, low-to-high-level output	T/R	Bn	$\begin{split} &V_{I}(An)=5\text{ V, CS at }0.8\text{ V,}\\ &R_{L}1=18\Omega\text{, }C_{L}=30\text{ pF,}\\ &R_{L}2\text{ not connected, }V_{L}=2\text{ V,}\\ &\text{See Figure }3, \end{split}$			25	no
t _{PHL3}	Propagation delay time, high-to-low-level output	1/K	DII				35	ns
tTLH	Transition time, low-to-high-level output	An	Bn	$\overline{\text{CS}}$ at 0.8 V, T/ $\overline{\text{R}}$ at 2 V, V _L = 2 V, C _L = 30 pF, R _L 1 = 18 Ω , R _L 2 not connected, See Figure 2	1	3	11	ns
tTHL	Transition time, high-to-low-level output	All			1	3	6	115

[†] Typical values are at V_{CC} = 5 V, T_A = 25°C



SN75ALS056, SN75ALS057 TRAPEZOIDAL-WAVEFORM INTERFACE BUS TRANSCEIVERS

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switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	SN75AI RECE		UNIT
		(MFUI)	(301701)		MIN	MAX	
^t PLH4	Propagation delay time, low-to-high-level output	Bn	An	$\overline{\text{CS}}$ at 0.8 V, T/ $\overline{\text{R}}$ at 0.8 V, R _L 1 = 390 Ω,		18	
^t PHL4	Propagation delay time, high-to-low-level output	ы	All	R_L 2 = 1.6 kΩ, C_L = 30 pF, See Figure 4			
^t PLZ1	Output disable time from low level	T/R	An	$\overline{\text{CS}}$ at 0.8 V, $V_{\text{I}(Bn)}$ = 2 V, V_{L} = 5 V, R _L 1 = 390 Ω , R _L 2 not connected, C _L = 15 pF, See Figure 3		20	ns
^t PZL1	Output enable time to low level	T/R	An	$\overline{\text{CS}}$ at 0.8 V, V _{I(Bn)} = 2 V, V _L = 5 V, R _L 1 = 390 Ω, R _L 2 = 1.6 kΩ, C _L = 30 pF, See Figure 3		40	ns
^t PHZ1	Output disable time from high level	T/R	An	$\overline{\text{CS}}$ at 0.8 V, $V_{\text{I}(\text{Bn})}$ = 0, V_{L} = 0, R_{L} 1 = 390 Ω , R_{L} 2 not connected, C_{L} = 15 pF, See Figure 3		17	ns
^t PZH1	Output enable time to high level	T/R	An	$\overline{\text{CS}}$ at 0.8 V, VI _(Bn) = 0, V _L = 0, R _L 1 not connected, R _L 2 = 1.6 kΩ, C _L = 30 pF, See Figure 3		15	ns
^t PLZ2	Output disable time from low level	cs	An	Bn at 2 V, T/\overline{R} at 0.8 V, $C_L = 5$ pF, $V_L = 5$ V, $R_L 1 = 390 \Omega$, $R_L 2$ not connected, See Figure 5		18	ns
^t PZL2	Output enable time to low level	cs	An	Bn at 2 V, T/\overline{R} at 0.8 V, C_L = 30 pF, V_L = 5 V, R_L 1 = 390 Ω , R_L 2 = 1.6 k Ω , See Figure 5		15	ns
^t PHZ2	Output disable time from high level	cs	An	Bn at 0.8 V, T/\overline{R} at 0.8 V, $C_L = 5$ pF, $V_L = 0$, $R_L 1 = 390 \Omega$, $R_L 2$ not connected, See Figure 5		8	ns
^t PZH2	Output enable time to high level	cs	An	Bn at 0.8 V, T/\overline{R} at 0.8 V, $C_L = 30$ pF, $V_L = 0$, $R_L 1$ not connected, $R_L 2 = 1.6$ k Ω , See Figure 5		17	ns
t _{w(NR)}	Receiver noise rejection pulse duration	Bn	An	$\overline{\text{CS}}$ at 0.8 V, T/ $\overline{\text{R}}$ at 0.8 V, R _L 1 = 390 Ω, R _L 2 = 1.6 kΩ, C _L = 30 pF, V _L = 5 V, See Figure 6	3		ns



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switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER		TO	TEST CONDITIONS	SN75ALS057 DRIVER			UNIT
		(INPUT)	(OUTPUT)		MIN	TYP [†]	MAX	
tPLH1	Propagation delay time, low-to-high-level output	π	Pn	Dn, En, \overline{RE} at 2 V, $V_L = 2$ V,			24	, no
tPHL1	Propagation delay time, high-to-low-level output	15		R _L 2 not connected, R _L 1 = 18 Ω , See Figure 2, C _L = 30 pF			20	ns
tPLH2	Propagation delay time, low-to-high-level output	Dn or En	Bn	$\overline{\text{TE}}$ at 0.8 V, $\overline{\text{RE}}$ at 2 V, V _L = 2 V, R _L 1 = 18 Ω , R _L 2 not connected,C _L = 30 pF, See Figure 2			19	
tPHL2	Propagation delay time, high-to-low-level output	DITOLEI					18	ns
tTLH	Transition time, low-to-high-level output	Dn or En	Bn	$\overline{\text{RE}}$ at 2 V, V _L = 2 V, $\overline{\text{TE}}$ at 0.8 V, R _L 1 = 18 Ω ,, R _L 2 not connected, C _L = 30 pF, See Figure 2	1	3	11	no.
tTHL	Transition time, high-to-low-level output	ווטו בוו			1	3	6	ns

[†] Typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (continued)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	SN75ALS057 RECEIVER		UNIT
		(1141 01)	(0011 01)		MIN	MAX	
^t PLH4	Propagation delay time, low-to-high-level output	Bn	Rn	RE at 0.8 V, TE at 2 V, $V_L = 5 \text{ V}$,	18		ns
^t PHL4	Propagation delay time, high-to-low-level output	ы	KII	RL1 = 390 Ω ,, RL2 = 1.6 k Ω ,, CL = 30 pF, See Figure 4		18	115
tPLZ2	Output disable time from low level	RE	Rn	Bn at 2 V, $\overline{\text{TE}}$ at 2 V, $V_L = 5$ V, $C_L = 5$ pF, $R_L 1 = 390 \Omega$, $R_L 2$ not connected, See Figure 5		18	ns
tPZL2	Output enable time to low level	RE	Rn	Bn at 2 V, $\overline{\text{TE}}$ at 2 V, V_L = 5 V, C_L = 30 pF, R_L 1 = 390 Ω , R_L 2 = 1.6 k Ω , See Figure 5		15	ns
^t PHZ2	Output disable time from high level	RE	Rn	Bn at 0.8 V, $\overline{\text{TE}}$ at 2 V, $V_L = 0$, $C_L = 5 \text{ pF}$, $R_L = 390 \Omega$, $R_L = 390 \Omega$, Respectively.		17	ns
^t PZH2	Output enable time to high level	RE	Rn	Bn at 0.8 V, $\overline{\text{TE}}$ at 2 V, $V_L = 0$, $C_L = 30$ pF, $R_L 1$ not connected, $R_L 2 = 1.6$ k Ω , See Figure 5		17	ns
tw(NR)	Receiver noise rejection pulse duration	Bn	Rn	$\overline{\text{TE}}$ at 2 V, $\overline{\text{RE}}$ at 0.8 V, V _L = 0, R _L 1 = 390 Ω, R _L 2 = 1.6 kΩ, C _L = 30 pF, See Figure 6	3		ns

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switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (continued)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	SN75AL DRIVER RECEI	PLUS	UNIT
					MIN	MAX	
tPLH6	Propagation delay time, low-to-high-level output	Dn	Rn	$\overline{\text{RE}}$ at 0.8 V, $\overline{\text{TE}}$ at 0.8 V, $R_L 1 = 390 \Omega$,		40	ne
tPHL6	Propagation delay time, high-to-low-level output	БП	Kii	$R_L 2 = 1.6 \text{ k}\Omega$, $C_L = 30 \text{ pF}$, See Figure 7		40	ns

PARAMETER MEASUREMENT INFORMATION

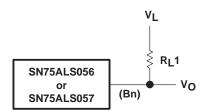
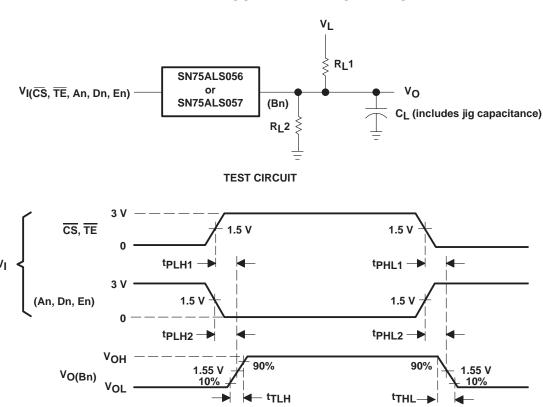


Figure 1. Driver Low-Level-Output-Voltage Test Circuit

PARAMETER MEASUREMENT INFORMATION

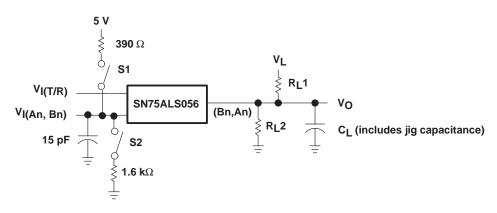


NOTE A: $t_r = t_f \le 5$ ns from 10% to 90%

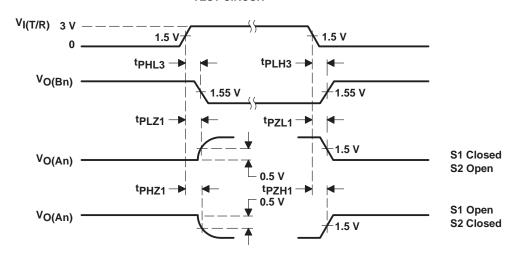
Figure 2. Driver Test Circuit and Voltage Waveforms

VOLTAGE WAVEFORMS

PARAMETER MEASUREMENT INFORMATION



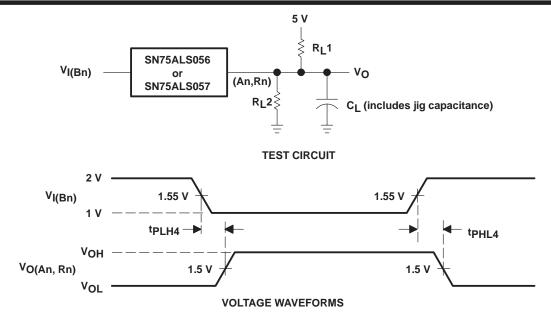
TEST CIRCUIT



VOLTAGE WAVEFORMS

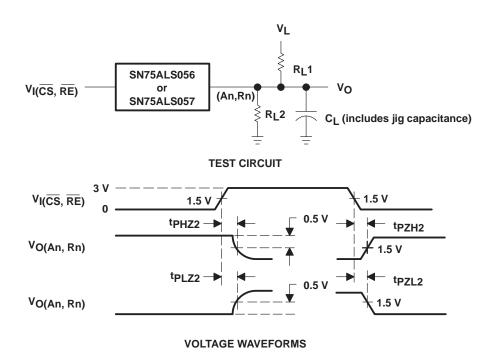
NOTE A: $t_r = t_f \le 5$ ns from 10% to 90%

Figure 3. Propagation Delay From T/R to An or Bn Test Circuit and Voltage Waveforms



NOTE A: $t_r = t_f \le 5$ ns from 10% to 90%

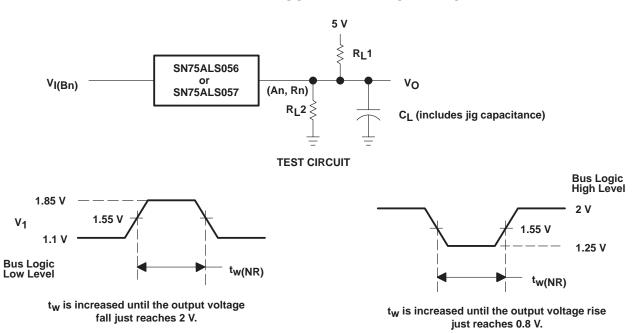
Figure 4. Receiver Test Circuit and Voltage Waveforms



NOTE A: $t_f = t_f \le 5$ ns from 10% to 90%

Figure 5. Propagation Delay From CS to An or RE to Rn Test Circuit and Voltage Waveforms

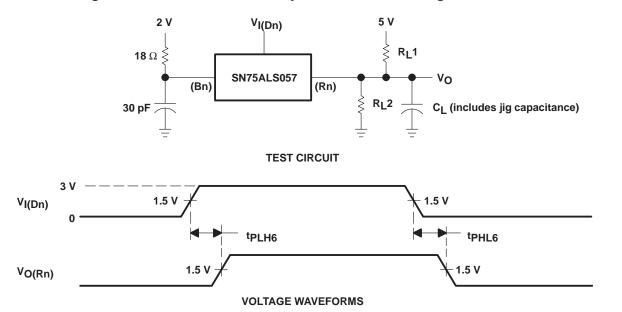
PARAMETER MEASUREMENT INFORMATION



VOLTAGE WAVEFORMS

NOTE A: $t_r = t_f \le 5$ ns from 10% to 90%

Figure 6. Receiver Noise-Immunity Test Circuit and Voltage Waveforms



NOTE A: $t_f = t_f \le 5$ ns from 10% to 90%

Figure 7. Driver Plus Receiver Delay-Times Test Circuits and Voltage Waveforms



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN75ALS056DW	LIFEBUY	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75ALS056	
SN75ALS057DW	LIFEBUY	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75ALS057	
SN75ALS057DWR	LIFEBUY	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75ALS057	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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TAPE AND REEL INFORMATION





		Dimension designed to accommodate the component width
		Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
Γ	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN75ALS057DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN75ALS057DWR	SOIC	DW	20	2000	350.0	350.0	43.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN75ALS056DW	DW	SOIC	20	25	506.98	12.7	4826	6.6
SN75ALS057DW	DW	SOIC	20	25	506.98	12.7	4826	6.6



SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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